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2823

PATENT
Atty. Dkt. No. AMAT/2966.P2/DSM/BSVD/JW

#15

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re Application of: Huang

Serial No.: 09/270,039

Confirmation No.: 0424

Filed: March 16, 1999

For: IN SITU DEPOSITION OF A LOW K DIELECTRIC LAYER, BARRIER LAYER, ETCH STOP AND ANTI-REFLECTIVE COATING FOR DAMASCENE APPLICATION

Group Art: 2823

Examiner: G. Fourson

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Response
8/13/02

Commissioner for Patents
Washington, D.C. 20231

CERTIFICATE OF MAILING
37 CFR 1.8

I hereby certify that this correspondence is being deposited on July 25, 2002 with the United States Postal Service as First Class Mail in an envelope addressed to: Commissioner for Patents, Washington, D.C. 20231.

7/25/02 (Date) — [signature] (Signature)

Dear Sir:

**RESPONSE TO OFFICE ACTION DATED APRIL 25, 2002**

In response to the Office Action dated April 25, 2002, having a shortened statutory period for response set to expire on July 25, 2002, please enter the following amendments and reconsider the claims pending in the application for reasons discussed below. Although Applicant believes that no fee is due in conjunction with this response, the Commissioner is hereby authorized to charge counsel's Deposit Account No. 20-0782/AMAT/2966P2/DD/BCVS/KMT, for any fees, including extension of time fees or excess claim fees, required to make this response timely and acceptable to the Office.

**THE PENDING CLAIMS:**

14. A method of forming a silicon carbide layer on a substrate, comprising:
introducing silicon, carbon, and a noble gas into a chamber;
initiating a plasma in the chamber;



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